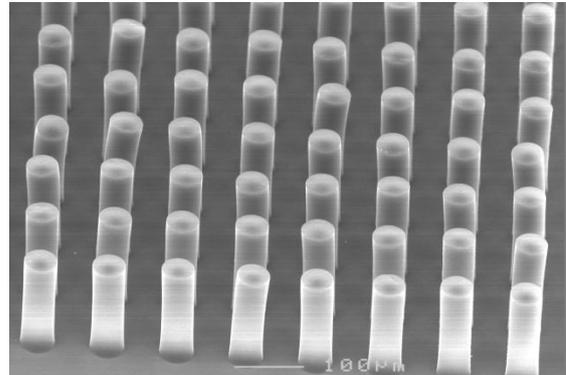
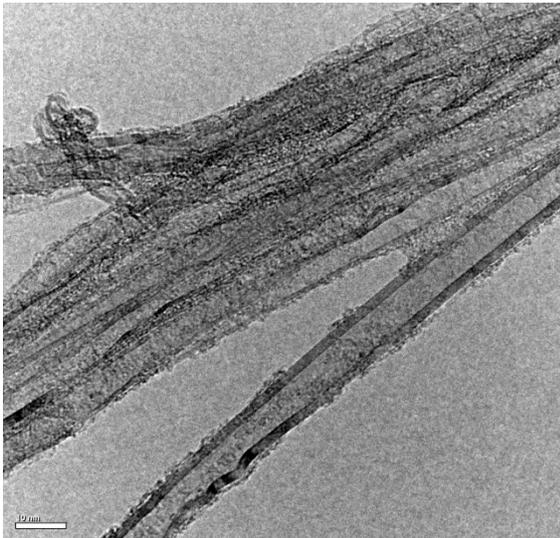


SHT CVD CNTs

DESCRIPTION

SHT offers production of carbon nanotubes at low pressure using chemical vapor deposition method. We can fabricate CNTs on various substrates such as Si, SiO₂, metals and flexible substrates with vertically aligned structures. CNTs both in forest and single manner are available by TCVD and PECVD, respectively. The CNTs offer very good uniformity on height and diameter. We can supply CNT structures from chip-sized up to 2 inch wafer. We also offer patterning and transferring service as required by our customers. More detailed info is available in the following table.



FEATURES AND BENEFITS

- Applicable on Si, metal and polymeric substrates
- In single, bundle and forest fashion
- Length and diameter controllable
- Low thermal contact resistance
- Easy to use
- High reliability

TYPICAL APPLICATIONS

- Composite
- Electrode
- Bumping
- Switch
- Capacitor

TYPICAL PROPERTIES OF SHT CVD CNTs

PROPERTY	
Color	Black
Thickness (μm)	1 - 500
Diameter (nm)	10-100
Electrical resistivity (Ω·m)	6.54×10^{-5}
Morphology	DWNTs and MWNTs
Area	Single, bundle, up to 2 inch wafer
Substrate	Si, SiO ₂ , ceramic, metals and polymeric substrates

SHT Smart High Tech AB

www.sht-tek.com

henric@sht-tek.com, Tel: +46 709 28 40 36

Aschebergsgatan 46, 411 33 Gothenburg, Sweden

